Product Specification

QNM7426

30V N-Channel MOSFET

Description

- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge

FEATURES

- 30V, 52A

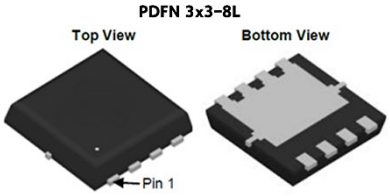
  $R_{DS(ON)}$ Typ = 4.1mΩ @ V_{GS} = 10V

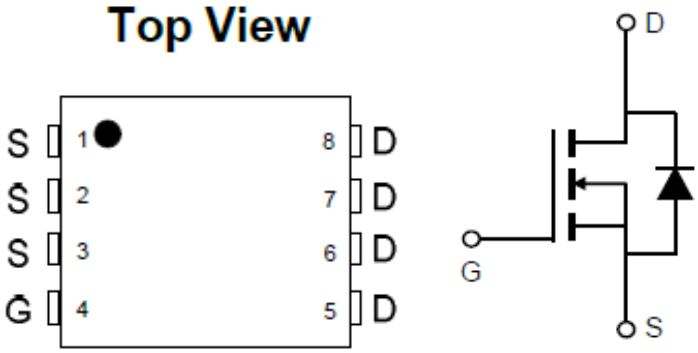
  $R_{DS(ON)}$ Typ = 6.2mΩ @ V_{GS} = 4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free

Applications

- Load Switch
- PWM Application
- Power Management

Pin Description





NO.	Symbol	Description
1	S	SOURCE
2	S	SOURCE
3	S	SOURCE
4	G	GATE
5	D	DRAIN
6	D	DRAIN
7	D	DRAIN
8	D	DRAIN

Absolute Maximum Ratings

(@ T_C = 25℃ unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		30	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	52	A
		T_C = 100℃	31.2	
I_{DM}	Pulsed Drain Current (1)		208	A
E_{AS}	Single Pulsed Avalanche Energy (2)		72	mJ
P_D	Power Dissipation	T_C = 25℃	35	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)		43	℃/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		3.6	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	℃

Electrical Characteristics

(T_J = 25℃ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D=250uA, V_{GS}=0V	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V	-	-	1.0	uA
I_{GSS}	Gate-Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1.0	1.4	2.5	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS}=10V, I_D=20A	-	4.1	5.3	mΩ
		V_{GS}=4.5V, I_D=10A	-	6.2	7.1	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz	-	1788	-	pF
C_{oss}	Output Capacitance		-	225	-	pF
C_{rss}	Reverse Transfer Capacitance		-	180	-	pF
Q_g	Total Gate Charge	V_{GS}=0~10V V_{DS}=15V, I_D=30A	-	34	-	nC
Q_{gs}	Gate Source Charge		-	6.5	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	7.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DD}=15V I_D=30A, R_{GEN}=3Ω	-	7	-	ns
t_r	Turn-On Rise Time		-	14	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	34	-	ns
t_f	Turn-Off Fall Time		-	11	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	52	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	160	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S=30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F=20A, di/dt=100A/us	-	10	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	1.7	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25℃, V_{DD}=15V, V_G=10V, R_G=25Ω, L=0.5mH, I_{AS}=16A

3. $R_{\theta JA}$ is measured with the device mounted on a 1 $inch^2$ pad of 2oz copper FR4 PCB

4. Pulse Test: Pulse Width≤300us, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Output Characteristics

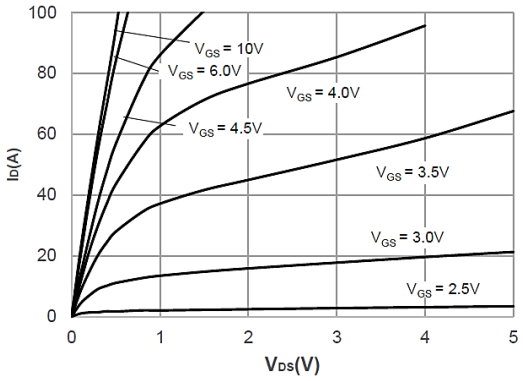


Figure 2: Typical Transfer Characteristics

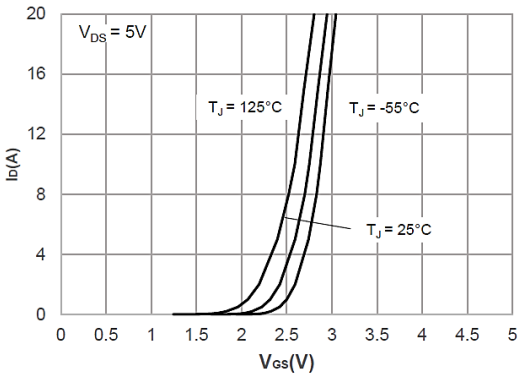


Figure 3: On-resistance vs. Drain Current

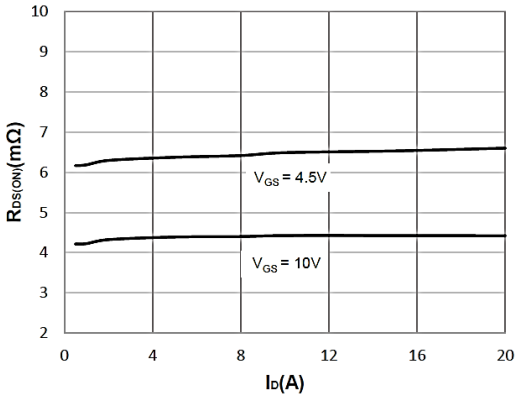


Figure 4: Body Diode Characteristics

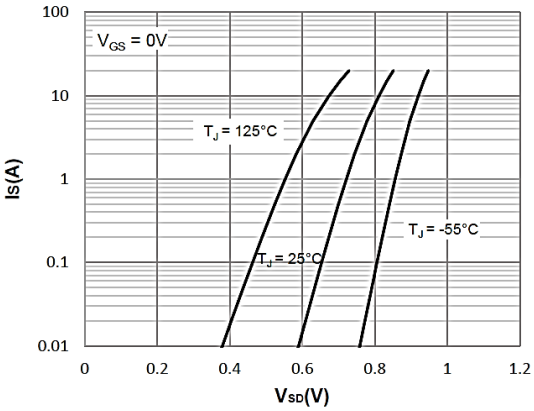


Figure 5: Gate Charge Characteristics

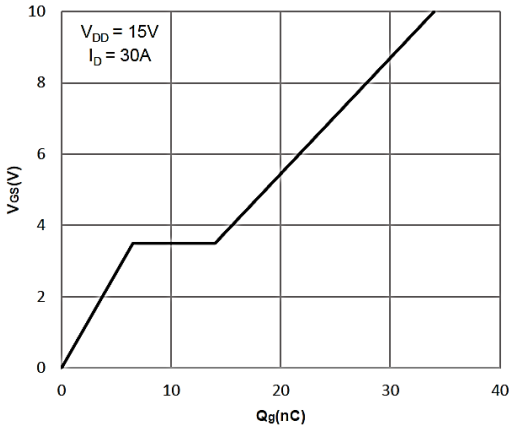


Figure 6: Capacitance Characteristics

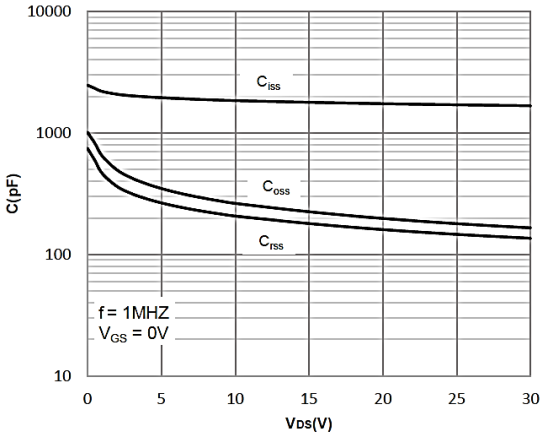


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

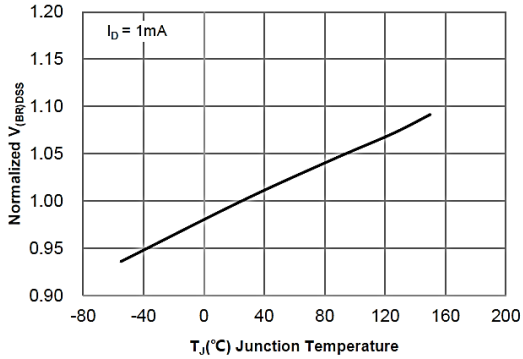


Figure 8: Normalized on Resistance vs. Junction Temperature

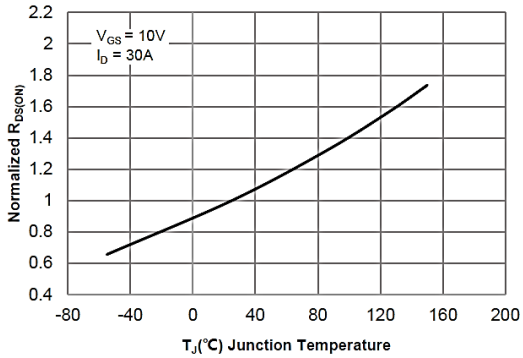


Figure 9: Maximum Safe Operating Area

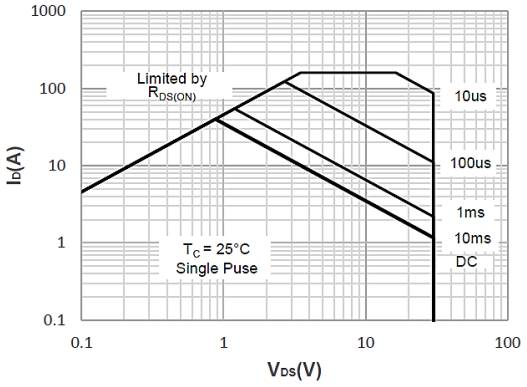


Figure 10: Maximum Continuous Drian Current vs. Case Temperature

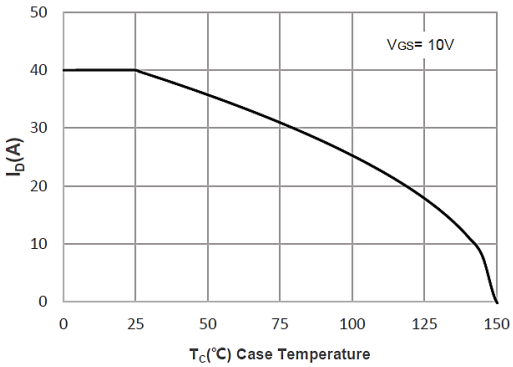


Figure 11: Normalized Maximum Transient Thermal Impedance

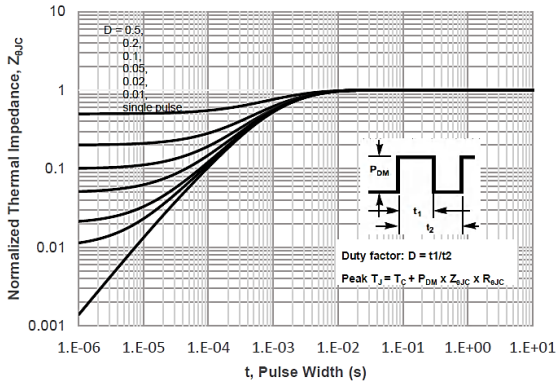
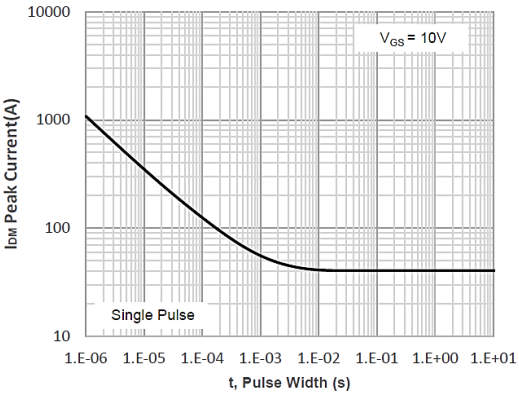


Figure 12: Peak Current Capacity



Test Circuit

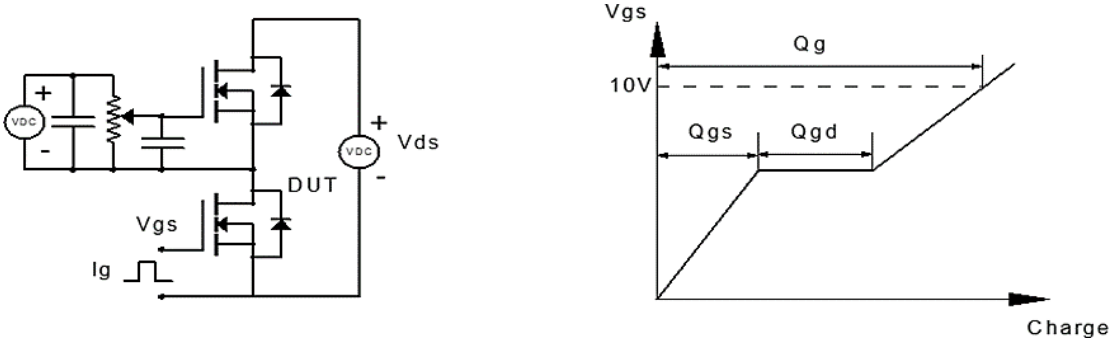


Figure 1: Gate Charge Test Circuit & Waveform

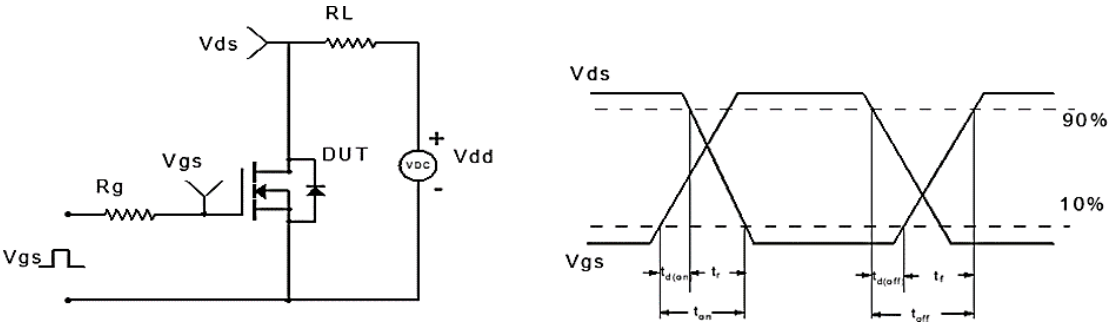


Figure 2: Resistive Switching Test Circuit & Waveform

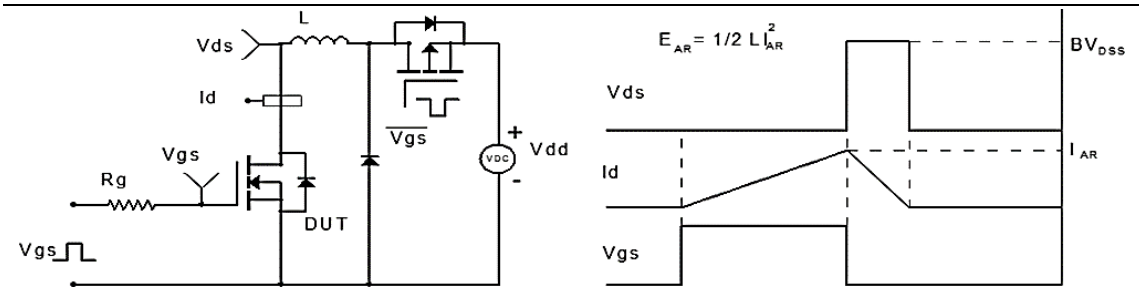


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

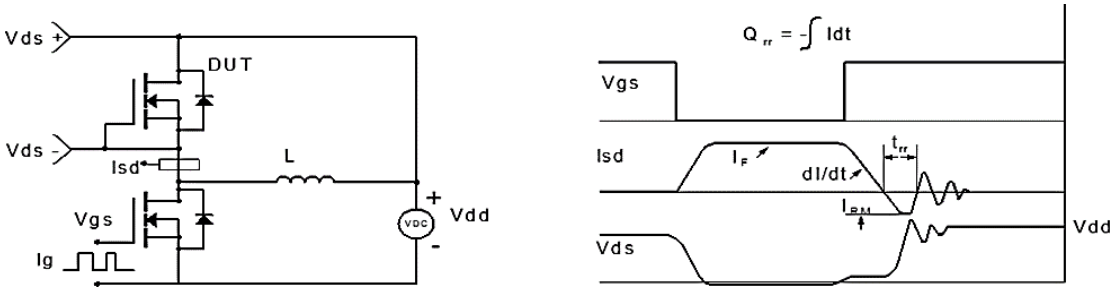
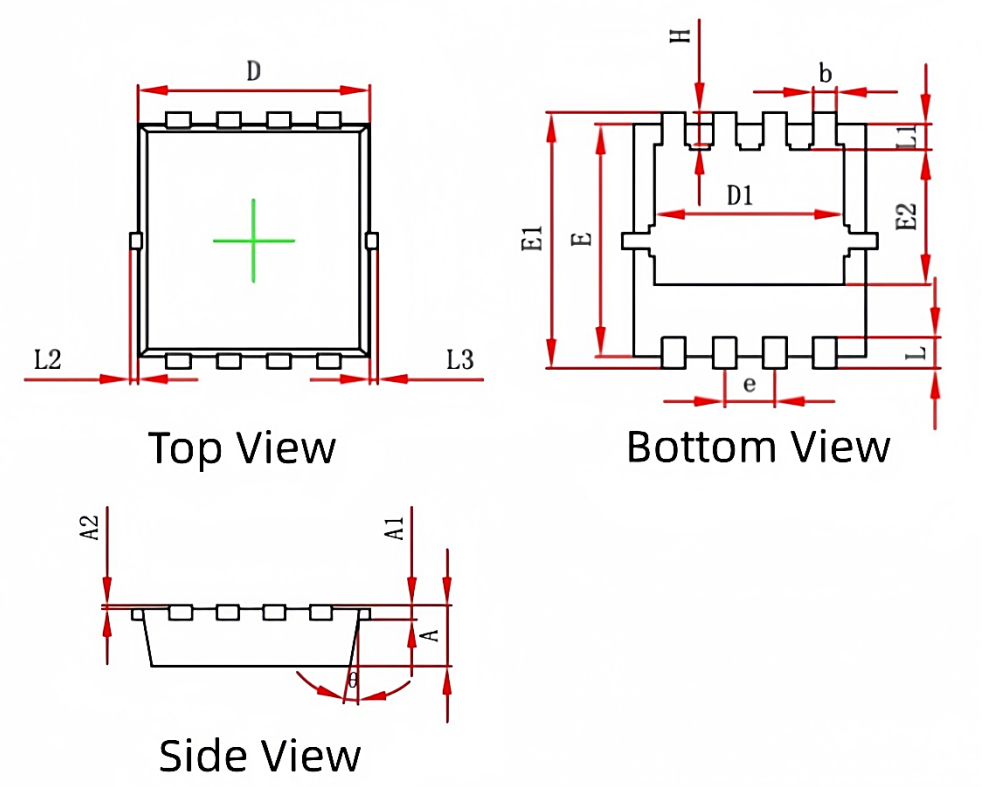
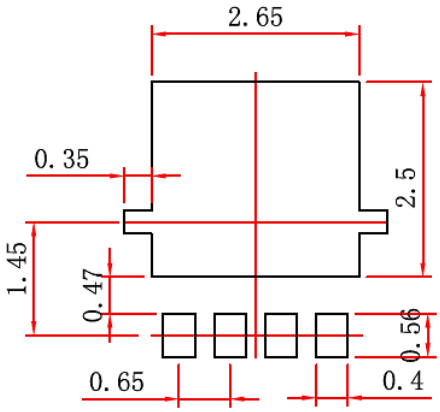


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN 3x3-8)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°



Note:

1.Controlling dimension: in millimeters.

2.General tolerance: ±0.05mm.

3.The pad layout is for reference purposes only.

Ordering information

Order Code	Package	V_{DS}(V)	I_D(A)	$R_{DS(ON)}$(mΩ)	
QNM7426	PDFN 3x3-8	30	52	V_{GS}=10V	4.1
				V_{GS}=4.5V	6.2